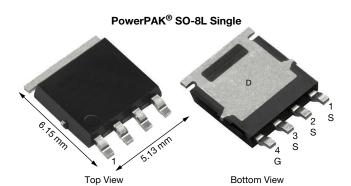


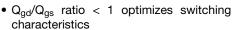
N-Channel 25 V (D-S) MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	25				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00074				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00140				
Q _g typ. (nC)	39				
I _D (A) ^a	201				
Configuration	Single				

FEATURES

- TrenchFET® Gen IV power MOSFET
- \bullet Tuned for the lowest $R_{DS}\text{-}Q_{oss}$ FOM
- 100 % Rq and UIS tested

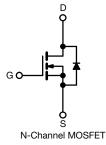






APPLICATIONS

- · Synchronous rectification
- High power density DC/DC
- Hot-swap switch and OR-ing FET
- · Battery and load switch



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiJA22DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unles	s otherwise not	ted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	25	V	
Gate-source voltage		V _{GS}	+20, -16	V	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		201		
	T _C = 70 °C	Ι , Γ	161		
	T _A = 25 °C	l _D	64 ^{b, c}	•	
	T _A = 70 °C	1	51 ^{b, c}		
Pulsed drain current (t = 100 μs)	I _{DM}	160	Α		
Continuous source-drain diode current	T _C = 25 °C		43.6		
	T _A = 25 °C	l _S	4.3 b, c	,	
Single pulse avalanche current		I _{AS}	50		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	125	mJ	
	T _C = 25 °C		48]	
Maximum power dissipation	T _C = 70 °C]	30.7	W	
	T _A = 25 °C	P _D	4.8 b, c	VV	
	T _A = 70 °C	1	3 b, c		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) d, e			260	-0	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R _{thJA}	22	26	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.7	2.6	C/VV

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

 Rework conditions: manual soldering with a soldering iron is not recommended for leadless component Maximum under steady state conditions is 70 °C/W



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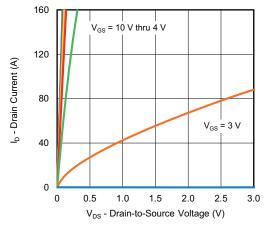
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	1		<u> </u>			
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	25	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	15.8	-	1406
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5.1	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.1	-	2.2	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +20, -16 \text{ V}$	-	-	± 100	nA
7		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μΑ
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30	-	-	Α
D		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	0.00057	0.00074	
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	-	0.00103	0.00140	Ω
Forward transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 25 \text{ A}$	-	155	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	6500	-	
Output capacitance	C _{oss}		-	2250	-	рF
Reverse transfer capacitance	C _{rss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz - 202				
C _{rss} /C _{iss} ratio	133		-	0.031	-	
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 15 A	-	83	125	
Total gate charge	Q _g	30 1 00 1 2	-	39	59	
Gate-source charge	Q _{as}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$	-	18	-	nC
Gate-drain charge	Q _{qd}		-	9.8	-	
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	-	57	86	
Gate resistance	R _q	f = 1 MHz	0.2	1.0	2.0	Ω
Turn-on delay time	t _{d(on)}		-	15	30	
Rise time	t _r	V_{DD} = 10 V, R_L = 1 Ω	-	6	12	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	39	80	
Fall time	t _f		-	6	12	
Turn-on delay time	t _{d(on)}		-	37	80	ns
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$	-	78	160	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	_	41	80	
Fall time	t _f			15	30	
Drain-Source Body Diode Characteristic	es ·				l l	
Continuous source-drain diode current	I _S	T _C = 25 °C	<u> </u>	-	43.6	
Pulse diode forward current (t = 100 μs)	I _{SM}	-	<u> </u>	-	160	Α
Body diode voltage	V _{SD}	I _S = 10 A	-	0.74	1.1	V
Body diode reverse recovery time	t _{rr}	<u> </u>	-	50	100	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	60	120	nC
Reverse recovery fall time	t _a	$T_J = 25 \text{ °C}$	-	27	-	
Reverse recovery rise time	t _b		_	23	 _ 	ns

Notes

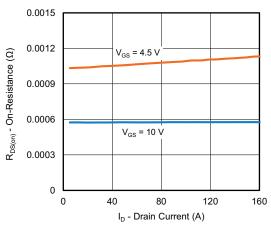
- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

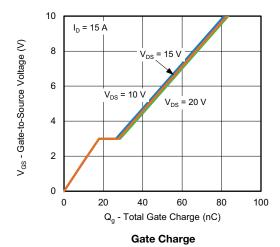


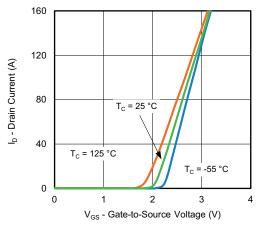


Output Characteristics

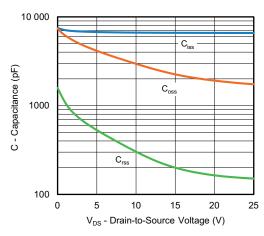


On-Resistance vs. Drain Current

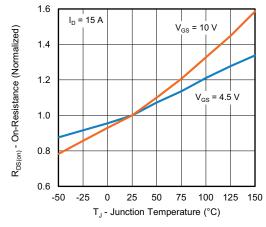




Transfer Characteristics

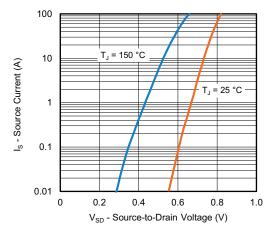


Capacitance

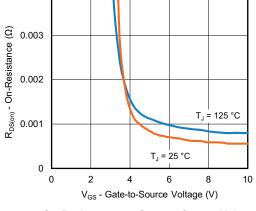


On-Resistance vs. Junction Temperature



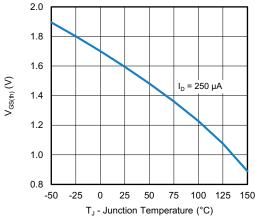


Source-Drain Diode Forward Voltage

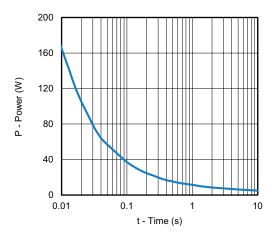


0.004

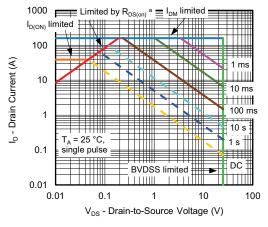
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

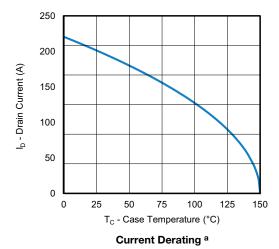


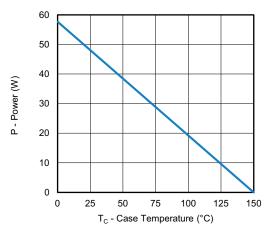
Single Pulse Power, Junction-to-Ambient



Safe Operating Area





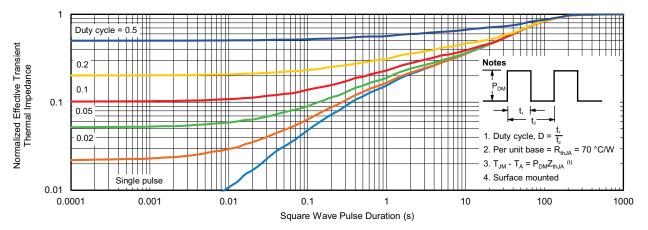


Power, Junction-to-Case

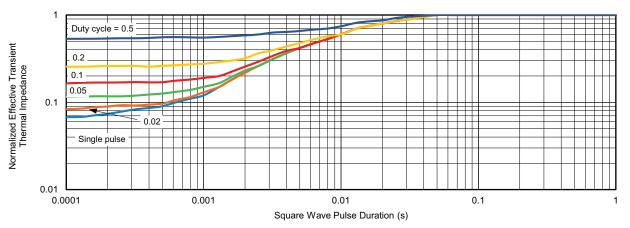
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient

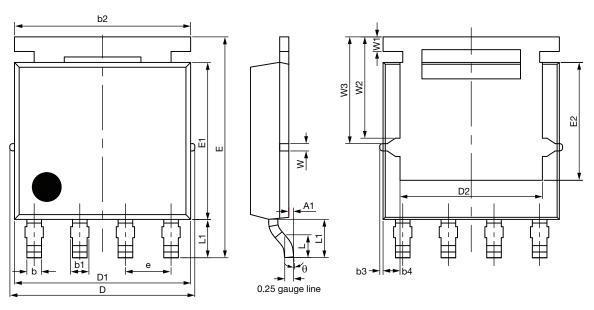


Normalized Thermal Transient Impedance, Junction-to-Case

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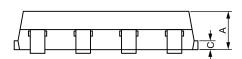


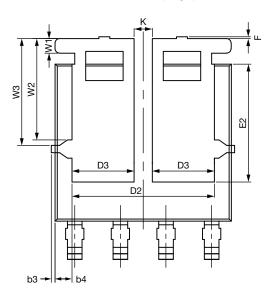
PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.238 0.242		
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51	•		0.020		
W	0.23				0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. E, 05-Aug-2019

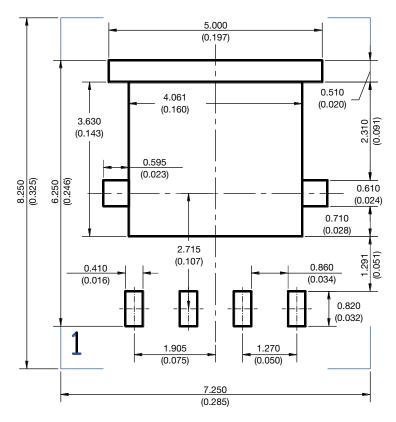
DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



Vishay

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